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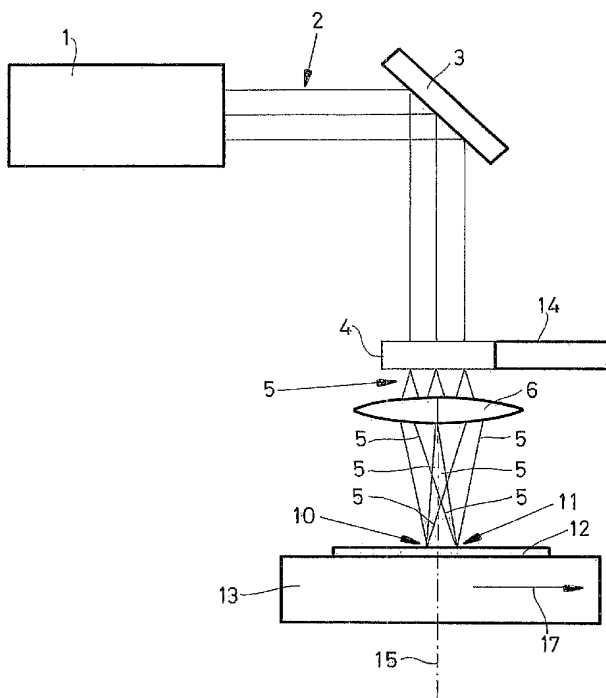
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(54) Title: METHOD, DEVICE AND DIFFRACTION GRATING FOR SEPARATING SEMICONDUCTOR ELEMENTS
FORMED ON A SUBSTRATE BY ALTERING SAID DIFFRACTION GRATING



(57) Abstract: The present document relates to a method of separating semiconductor elements formed in a wafer (12) of semiconductor material using a laser (1) producing a primary laser beam (2). Said at least one primary laser beam (2) is split into a plurality of secondary laser beams (5) using a first diffraction grating (4, 14) having at least a first grating structure relative to said wafer (12), by impinging said at least one primary laser beam (2) on said first grating structure (4, 14). At least one first score is formed by moving said laser (1) relative to said wafer (12) in a first direction. The method further comprises a step of forming at least one second score by moving said (1) laser relative to said wafer (12) in a second direction. Before the step of moving said laser (1) relative to said wafer (12) in the second direction, the method comprises a step of altering said first grating structure (4, 14) to a second grating structure (4, 14) relative to said wafer. An arrangement and diffraction grating (4, 14) for use in this method are also disclosed.



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